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N - Channel 40 V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | |
|---------------------|----------------------------------|---------------------------------|-----------------------|--|--|
| V _{DS} (V) | $R_{DS(on)}$ (m Ω)(Typ.) | I _D (A) ^a | Q _g (Typ.) | | |
| 40 | 4.5 at V _{GS} = 10 V | 40 | 20.9 nC | | |
| 40 | 6.6 at V _{GS} = 4.5 V | 40 | 20.9 110 | | |

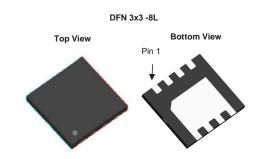
FEATURES

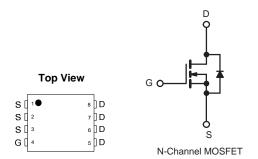
- DT-Trench MOSFET
- 100 % R_g and UIS Tested
- Low RDS(ON)
- · High Current Capability
- · AEC-Q101 Qualified for Automotive Applications



APPLICATIONS

- · Battery charging and discharging for battery pack
- · Power switch for Adaptor/ Charger





| ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted) | | | | | |
|--|-----------------------------------|----------------|------|---|--|
| PARAMETER | SYMBOL | LIMIT | UNIT | | |
| Drain-Source Voltage | V _{DS} | 40 | V | | |
| Gate-Source Voltage | V _{GS} | ± 20 | v | | |
| Continuous Drain Current /T 175 °C\2 | T _C = 25 °C | | 40 | | |
| Continuous Drain Current (T _J = 175 °C) ^a | T _C = 100 °C | I _D | 28.9 | Α | |
| Pulsed Drain Current ^b | I _{DM} | 140 | | | |
| Single Avalanche Energy | E _{AS} | 85 | mJ | | |
| Mayimum Dawar Dissination(| T _C = 25 °C | В | 35 | W | |
| Maximum Power Dissipation ^c | T _C = 100 °C | P _D | 17.5 | | |
| Operating Junction and Storage Temperature R | T _J , T _{sta} | - 55 to +175 | °C | | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|-------------------|-------|------|--|--|
| PARAMETER | SYMBOL | LIMIT | UNIT | | |
| Junction-to-Ambient (PCB Mount) ^d | R _{thJA} | 55 | °C/W | | |
| Junction-to-Case (Drain) | R _{thJC} | 4.2 | | | |

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{8JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



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| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT | |
|---------------------------------------|--|---|------|------|-------|------|--|
| Static | | | | • | | | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | 40 - | | - | V | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | 1.0 | - | 3.0 | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | - | - | ± 100 | nA | |
| Zero Gate Voltage Drain Current | | $V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$ | - | - | 1 | | |
| zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 32 V, V _{GS} = 0 V, T _J = 55 °C - | | - | 10 | - μA | |
| On-State Drain Current ^a | On-State Drain Current ^a $I_{D(on)}$ $V_{DS} \ge 5 \text{ V}, V_{GS} = 5 \text{ V}$ | | 40 | - | - | Α | |
| Drain-Source On-State Resistance a | D | V _{GS} = 10 V, I _D = 20 A | - | 4.5 | 5.5 | mΩ | |
| Dialii-Source Oil-State nesistance " | R _{DS(on)} | V _{GS} = 4.5 V, I _D = 18 A | - | 6.6 | 8.4 | | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = 5 V, I _D = 10 A | - | 45 | - | S | |
| Dynamic ^b | | | | • | | | |
| Input Capacitance | C _{iss} | | - | 1270 | - | | |
| Output Capacitance | C _{oss} | V _{GS} = 0 V, V _{DS} = 20 V, f = 1 MHz | - | 480 | - | pF | |
| Reverse Transfer Capacitance | C _{rss} | | - | 19.9 | - | | |
| Total Gate Charge ^c | Qg | | - | 20.9 | - | | |
| Gate-Source Charge ^c | Q_{gs} | $V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$ | - | 2.7 | - | nC | |
| Gate-Drain Charge ^c | Q _{gd} | | - | 3.7 | - | | |
| Gate Resistance | R_g | f = 1 MHz | - | 3.8 | - | Ω | |
| Turn-On Delay Time ^c | t _{d(on)} | | - | 8.5 | - | | |
| Rise Time ^c | t _r | $V_{DS} = 20 \text{ V}, I_{D} = 20 \text{ A}, R_g = 1.5 \Omega$ | - | 3 | - | | |
| Turn-Off Delay Time ^c | t _{d(off)} | V _{GS} = 10 V | - | 20 | - | ns | |
| Fall Time ^c | t _f | | - | 4 | - | | |
| Drain-Source Body Diode Ratings and | Characterist | tics ^b (T _C = 25 °C) | | • | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | - | - | 40 | Α | |
| Pulsed Current (t = 100 μs) | I _{SM} | | - | - | 140 | Α | |
| Forward Voltage ^a | V_{SD} | I _F = 1 A, V _{GS} = 0 V | - | - | 1.2 | V | |
| Reverse Recovery Time | t _{rr} | L = 20 A di/dt = 100 A/vo | - | 12 | - | ns | |
| Reverse Recovery Charge | Q_{rr} | I _F = 20 A, di/dt = 100 A/μs | - | 25 | - | nC | |

Notes

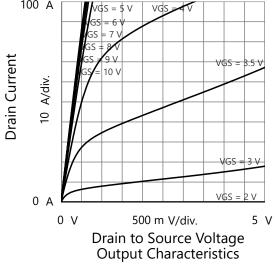
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

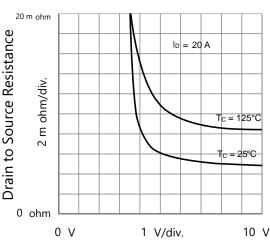
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



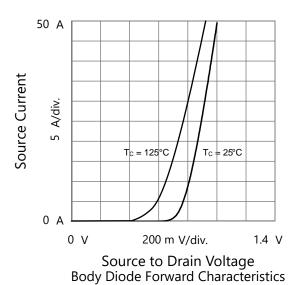
TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)

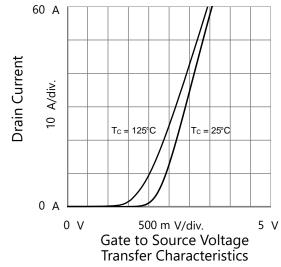
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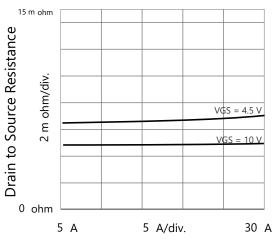


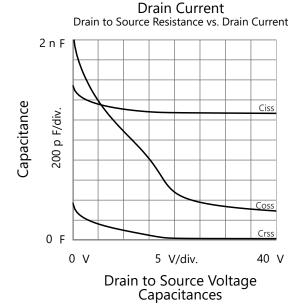


Gate to Source Voltage



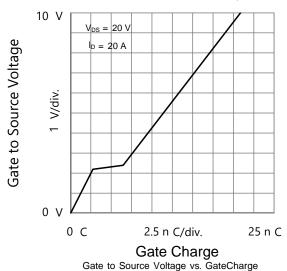


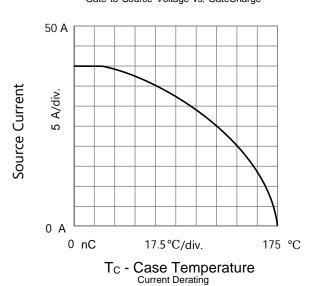


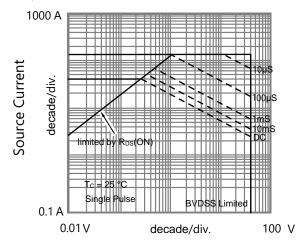


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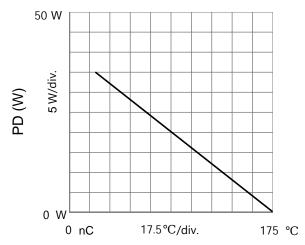
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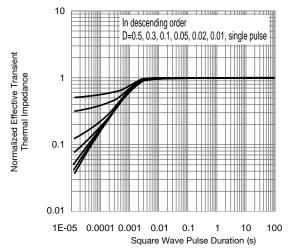


Source to Drain Voltage
Safe Operating Area, Junction-to-Ambient



T_C - Case Temperature

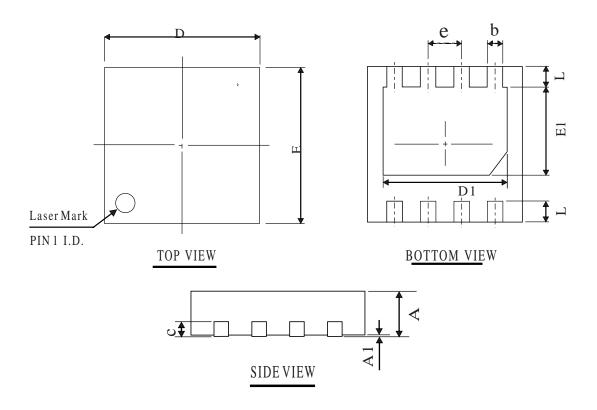
Power Derating



Normalized Thermal Transient Impedance, Junction-to-Case



DFN3*3-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=mm)

| SYMBOL | MIN | NOM | MAX |
|--------|------------|------|-------|
| Α | 0. 60 | 0.75 | 0. 90 |
| A1 | 0. 00 | 0.02 | 0. 08 |
| b | 0. 20 | 0.30 | 0.45 |
| D | 2. 85 | 3.00 | 3. 15 |
| Е | 2. 85 | 3.00 | 3. 15 |
| D1 | 2. 10 | 2.40 | 2.70 |
| E1 | 1.50 | 1.70 | 2.00 |
| L | 0. 20 | 0.40 | 0.60 |
| С | 0. 203 REF | | |
| e | 0. 65 BSC | | |

OTHER DIMENSIONS

| A | 0. 50 | 0.55 | 0.60 |
|---|-------|------|------|
| A | 0.40 | 0.45 | 0.50 |





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